

ABSTRACT

A method of fabricating a nonvolatile memory device is disclosed. First, a lower insulating layer and a sacrificial layer are formed in sequence on a substrate. Then, a sacrificial layer pattern is formed through removing some part of the sacrificial layer by an etching process to expose some part of the lower insulating layer. At the same time, spacers are formed on sidewalls of the sacrificial layer pattern. The spacers are formed of polymers resulting from the etching of the sacrificial layer. The exposed lower insulating layer is removed to form a lower insulating layer pattern. Next, the sacrificial layer pattern and the spacers are removed. Accordingly, linewidth of a tunnel window which defined by the insulating layer pattern becomes narrow.